

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	19	(Krull-Wade\$.in.	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L2	14834	((gate adj electrode) near20 (semiconductor adj device))	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L3	3826	L2 and (depletion)	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L4	1609	L3 and doping	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L5	689	L4 and (gate near10 dielectric)	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L6	678	L5 and (source or drain)	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L7	340	L6 and trench	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L8	109	L7 and (heat adj treat\$4)	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L9	50	L8 and (amorphous near10 silicon)	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L10	34	L9 and poly\$1silicon	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L11	34	L10 and boron	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L12	22	L11 and photoresist	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
L13	2	L1 and L12	US-PGPUB; USPAT	OR	OFF	2009/08/25 14:25
S1	5	((("6069061") or ("5837598") or ("6288403") or ("3607449") or ("5801086"))).PN.	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:32
S2	9976	((gate adj electrode) near20 (semiconductor adj device))	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:33

S3	2589	S2 and (depletion)	US-PGPUB; USPAT	OR	OFF	2006/11/09 08:08
S4	0	S3 and (ion adj implat\$4)	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:34
S5	1121	S3 and doping	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:34
S6	431	S5 and (gate near10 dielectric)	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:35
S7	424	S6 and (source or drain)	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:35
S8	43	S7 and asymmetric	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:16
S9	8	S8 and shallow	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:36
S10	2	S8 and (trench near10 isolation)	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:36
S11	197	S7 and trench	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:37
S12	64	S11 and (heat adj treat\$4)	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:37
S13	29	S12 and (amorphous near10 silicon)	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:38
S14	19	S13 and poly\$1silicon	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:38
S15	19	S14 and boron	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:43
S16	1	S14 and decaborane	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:44
S17	12	S15 and photoresist	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:44
S18	15	("20010020725"   "20020130378"   "20020185697"   "20030049919"   "4835112"   "5633177"   "5861340"   "5952692"   "6252283"   "6301155"   "6423632"   "6492694"   "6504214"   "6660660"   "6710407").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/08 10:57
S19	1	("6013332").PN.	US-PGPUB; USPAT	OR	OFF	2006/11/08 10:57
S20	1	("5885877").PN.	US-PGPUB; USPAT	OR	OFF	2006/11/08 15:25

S21	1	("5905293").PN.	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:15
S22	1	("7126199").PN.	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:15
S23	9986	((gate adj electrode) near20 (semiconductor adj device))	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:16
S24	2592	S23 and (depletion)	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:16
S25	1122	S24 and doping	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:16
S26	432	S25 and (gate near10 dielectric)	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:16
S27	425	S26 and (source or drain)	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:16
S28	227	S27 and ((gate adj electrode) near10 thickness)	US-PGPUB; USPAT	OR	OFF	2006/11/09 09:43
S29	1	("5773337").PN.	US-PGPUB; USPAT	OR	OFF	2006/11/09 11:12
S30	1	("6693051").PN.	US-PGPUB; USPAT	OR	OFF	2006/11/09 11:12
S31	11953	438/515,653,657,690,702,710,787,758,790;257/296,306,330.ccls.	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S32	9986	((gate adj electrode) near20 (semiconductor adj device))	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S33	2592	S32 and (depletion)	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S34	1122	S33 and doping	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S35	432	S34 and (gate near10 dielectric)	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S36	425	S35 and (source or drain)	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S37	198	S36 and trench	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S38	64	S37 and (heat adj treat\$4)	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S39	29	S38 and (amorphous near10 silicon)	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11

S40	19	S39 and poly\$1silicon	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S41	19	S40 and boron	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S42	12	S41 and photoresist	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:11
S43	19634	S31 and S42	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/11/09 16:12
S44	3	S31 and S42	US-PGPUB; USPAT	OR	OFF	2006/11/09 16:13
S45	0	(thin adj first adj gate adj electrode near5 pre\$1determined adj thickness near10 dielectric near10 interface near20 minimize adj gate adj depletion near10 interface)	US-PGPUB; USPAT	OR	OFF	2007/07/13 11:09
S46	1	("3607449").PN.	USPAT; USOCR	OR	OFF	2008/05/28 15:11
S47	1	("20060099812").PN.	US-PGPUB; USPAT	OR	OFF	2009/03/09 14:53

8/ 25/ 2009 2:27:19 PM

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